具有反向电流保护功能的 TPS737xx 1A 低压降稳压器

1 特性

- 与 1µF 或更大的陶瓷输出电容器搭配使用时可保持稳定
- 输入电压范围：2.2V 至 5.5V
- 超低压降：1A 时典型值为 130mV
- 即使使用仅为 1µF 的输出电容器，也能实现出色的负载瞬态响应
- NMOS 拓扑结构可提供低反向泄漏电流
- 初始精度为 1%
- 在线路、负载和温度范围内总精度为 3%
- 关断模式下，I_Q 典型值小于 20nA
- 热关断和电流限制可实现故障保护
- 提供多个输出电压版本
  - 可调节输出：1.20V 至 5.5V
  - 使用工厂封装级编程，可提供定制输出

2 应用

- 针对 DSP、FPGA、ASIC 和微处理器的负载点调节
- 针对开关电源的后置稳压
- 便携式和电池供电类设备

3 说明

TPS737xx 系列线性低压降 (LDO) 稳压器在电压跟随器配置中使用了 NMOS 旁路元件。该拓扑结构对输出电容值和等效串联电阻 (ESR) 的敏感度相对较低，从而实现多种负载配置。负载瞬态响应出色，即使与 1µF 小型陶瓷输出电容搭配工作时也是如此。NMOS 拓扑结构也可实现超低压降。

TPS737xx 系列利用先进的 BiCMOS 工艺实现高精度，同时提供超低的压降和低接地引脚电流。未启用时的电流消耗小于 20nA，适用于便携式 应用。这些器件受到热关断和折返电流限制的保护。

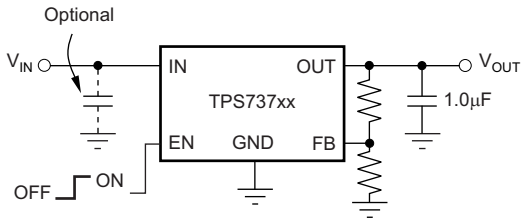
对于要求更高输出电压精度的 应用 ，请考虑 TI 的 TPS7A37xx 系列 1% 总精度、1A 低压降稳压器。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TPS737xx	VSON (8)	3.00mm × 3.00mm
	SOT-223 (6)	6.50mm × 3.50mm
	WSON (6)	2.00mm × 2.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

典型应用电路



本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。 有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。 TI 不保证翻译的准确性和有效性。 在实际设计之前，请务必参考最新版本的英文版本。

目录

1 特性 ... 1
2 应用 ... 1
3 说明 ... 1
4 修订历史记录 ... 2
5 Pin Configuration and Functions ... 4
6 Specifications ... 5
6.1 Absolute Maximum Ratings ... 5
6.2 ESD Ratings ... 5
6.3 Recommended Operating Conditions ... 5
6.4 Thermal Information ... 6
6.5 Electrical Characteristics ... 7
6.6 Typical Characteristics ... 8
7 Detailed Description ... 13
7.1 Overview ... 13
7.2 Functional Block Diagrams ... 13
7.3 Feature Description ... 14
7.4 Device Functional Modes ... 15
8 Application and Implementation ... 16
8.1 Application Information ... 16
8.2 Typical Application ... 16
8.3 What To Do and What Not To Do ... 18
9 Power Supply Recommendations ... 18
10 Layout ... 19
10.1 Layout Guidelines ... 19
10.2 Layout Example ... 21
11 器件和文档支持 ... 22
11.1 器件支持 ... 22
11.2 文档支持 ... 22
11.3 接收文档更新通知 ... 22
11.4 支持资源 ... 22
11.5 商标 ... 22
11.6 静电放电警告 ... 22
11.7 Glossary ... 23
12 机械、封装和可订购信息 ... 23

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision Q (May 2015) to Revision R — **Page**

- Changed WSON to VSON and VSON to WSON in header row of *Pin Functions* table ... 4
- Changed unit from *V* to *%* in V_{OUT} parameter of *Electrical Characteristics* table ... 7

Changes from Revision P (July 2013) to Revision Q — **Page**

- 已添加 添加了 *ESD 额定值* 表、*特性* *说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源相关建议* 部分、*布局* 部分、*器件和文档支持* 部分以及*机械、封装和可订购信息* 部分 ... 1
- Changed "free-air temperature" to "junction temperature" in *Absolute Maximum Ratings* condition statement ... 5
- Changed "free-air temperature" to "junction temperature" in *Recommended Operating Conditions* condition statement ... 5
- Changed Internal Reference parameter (V_{FB}) typical values from 1.2 V to 1.204 V ... 7

Changes from Revision O (June 2012) to Revision P — **Page**

- 已添加 向*说明* 部分添加了最后一段 ... 1

Changes from Revision N (June 2011) to Revision O — **Page**

- Changed Thermal Information table data and footnote 2b ... 6
- Changed V_{FB} *Internal reference* parameter in *Electrical Characteristics* table ... 7
- Changed title of Figure 6 ... 8

Changes from Revision M (October, 2010) to Revision N — **Page**

- Added footnote (3) to *Thermal Information* table ... 7
- Added footnote to Figure 38 ... 21

版权 © 2006–2019, Texas Instruments Incorporated

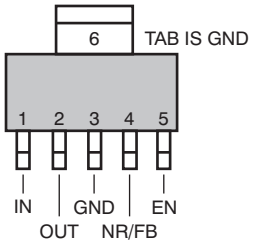
Changes from Revision L (August, 2010) to Revision M **Page**

- Corrected typo in Figure 38 21

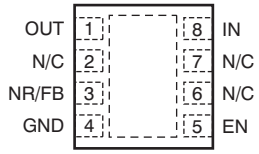
Copyright © 2006–2019, Texas Instruments Incorporated

5 Pin Configuration and Functions

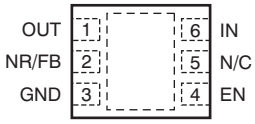
DCQ Package
6-Pin SOT-223
Top View



DRB Package
8-Pin VSON
Top View



DRV Package(1)
6-Pin WSON
Top View



(1) Power dissipation may limit operating range. Check *Thermal Information* table.

Pin Functions

PIN				I/O	DESCRIPTION
NAME	SOT-223	VSON	WSON		
IN	1	8	6	I	Unregulated input supply
GND	3, 6	4, Pad	3, Pad	—	Ground
EN	5	5	4	I	Driving the enable pin (EN) high turns on the regulator. Driving this pin low puts the regulator into shutdown mode. Refer to the *Enable Pin and Shutdown* section under *Application Information* for more details. EN must not be left floating and can be connected to IN if not used.
NR	4	3	2	—	Fixed voltage versions only—connecting an external capacitor to this pin bypasses noise generated by the internal bandgap, reducing output noise to very low levels.
FB	4	3	2	I	Adjustable voltage version only—this is the input to the control loop error amplifier, and is used to set the output voltage of the device.
OUT	2	1	1	O	Regulator output. A 1.0-μF or larger capacitor of any type is required for stability.
NC	—	2, 6, 7	5	—	Not connected

Copyright © 2006–2019, Texas Instruments Incorporated

6 Specifications

6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Voltage	V_{IN}	–0.3	6	V
	V_{EN}	–0.3	6	
	V_{OUT}	–0.3	5.5	
	V_{NR}, V_{FB}	–0.3	6	
Peak output current	I_{OUT}	Internally limited		
Output short-circuit duration		Indefinite		
Continuous total power dissipation	P_{DISS}	See *Thermal Information*		
Temperature	Junction range, T_J	–55	150	°C
	Storage range, T_{stg}	–65	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IN}	Input supply voltage range	2.2		5.5	V
I_{OUT}	Output current	0		1	A
T_J	Operating junction temperature	–40		125	°C

Copyright © 2006–2019, Texas Instruments Incorporated

6.4 Thermal Information

THERMAL METRIC(1)		TPS737xx(2)			UNIT
		DRB [VSON]	DCQ [SOT-223]	DRV [WSON](3)	
		8 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance(4)	49.5	53.1	67.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance(5)	58.9	35.2	87.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance(6)	25.1	7.8	36.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter(7)	1.7	2.9	1.8	°C/W
ψ_{JB}	Junction-to-board characterization parameter(8)	25.2	7.7	37.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance(9)	8.6	N/A	7.7	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC package thermal metrics* application report.
(2) Thermal data for the DRB, DCQ, and DRV packages are derived by thermal simulations based on JEDEC-standard methodology as specified in the JESD51 series. The following assumptions are used in the simulations:
  (a) i. DRB: The exposed pad is connected to the PCB ground layer through a 2 × 2 thermal via array.
  ii. DCQ: The exposed pad is connected to the PCB ground layer through a 3 × 2 thermal via array.
  iii. DRV: The exposed pad is connected to the PCB ground layer through a 2 × 2 thermal via array. Due to size limitation of thermal pad, 0.8-mm pitch array is used which is off the JEDEC standard.
  (b) The top copper layer has a detailed copper trace pattern. The bottom copper layer is assumed to have a 20% thermal conductivity of copper, representing a 20% copper coverage.
  (c) These data were generated with only a single device at the center of a JEDEC high-K (2s2p) board with 3-inch × 3-inch copper area. To understand the effects of the copper area on thermal performance, see the *Power Dissipation* and *Estimating Junction Temperature* sections of this data sheet.
(3) Power dissipation may limit operating range.
(4) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
(5) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the top of the package. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
(6) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
(7) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain θ_{JA} using a procedure described in JESD51-2a (sections 6 and 7).
(8) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain θ_{JA} using a procedure described in JESD51-2a (sections 6 and 7).
(9) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

Copyright © 2006–2019, Texas Instruments Incorporated

6.5 Electrical Characteristics

Over operating temperature range (T_J = –40°C to 125°C), V_{IN} = $V_{OUT(nom)}$ + 1 V(1), I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted. Typical values are at T_J = 25°C.

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IN}	Input voltage range(1)(2)			2.2		5.5	V
V_{FB}	Internal reference (DCQ package)		T_J = 25°C	1.198	1.204	1.21	V
	Internal reference (DRB and DRV packages)		T_J = 25°C	1.192	1.204	1.216	
V_{OUT}	Output voltage range (TPS73701)(3)			V_{FB}		5.5 – V_{DO}	V
	Accuracy(1),(4)	Nominal	T_J = 25°C	–1		1	%
			5.36 V < V_{IN} < 5.5 V, V_{OUT} = 5.08 V, 10 mA < I_{OUT} < 800 mA, –40°C < T_J < 85°C, TPS73701 (DCQ)	–2		2	
		Over V_{IN}, I_{OUT}, and T	V_{OUT} + 0.5 V ≤ V_{IN} ≤ 5.5 V; 10 mA ≤ I_{OUT} ≤ 1 A	–3	±0.5%	3	
$\Delta V_{OUT(\Delta VIN)}$	Line regulation(1)		$V_{OUT(nom)}$ + 0.5 V ≤ V_{IN} ≤ 5.5 V		0.01		%/V
$\Delta V_{OUT(\Delta IOUT)}$	Load regulation		1 mA ≤ I_{OUT} ≤ 1 A		0.002		%/mA
			10 mA ≤ I_{OUT} ≤ 1 A		0.0005		
V_{DO}	Dropout voltage(5) (V_{IN} = $V_{OUT(nom)}$ – 0.1 V)		I_{OUT} = 1 A		130	500	mV
$Z_{OUT(DO)}$	Output impedance in dropout		2.2 V ≤ V_{IN} ≤ V_{OUT} + V_{DO}		0.25		Ω
I_{CL}	Output current limit		V_{OUT} = 0.9 × $V_{OUT(nom)}$	1.05	1.6	2.2	A
I_{OS}	Short-circuit current		V_{OUT} = 0 V		450		mA
I_{REV}	Reverse leakage current(6) ($-I_{IN}$)		V_{EN} ≤ 0.5 V, 0 V ≤ V_{IN} ≤ V_{OUT}		0.1		µA
I_{GND}	GND pin current		I_{OUT} = 10 mA		400		µA
			I_{OUT} = 1 A		1300		
I_{SHDN}	Shutdown current [I_{GND}]		V_{EN} ≤ 0.5 V, V_{OUT} ≤ V_{IN} ≤ 5.5		20		nA
I_{FB}	FB pin current (TPS73701)				0.1	0.6	µA
PSRR	Power-supply rejection ratio (ripple rejection)		f = 100 Hz, I_{OUT} = 1 A		58		dB
			f = 10 kHz, I_{OUT} = 1 A		37		
V_n	Output noise voltage BW = 10 Hz to 100 kHz		C_{OUT} = 10 µF		27 × V_{OUT}		μV_{RMS}
t_{STR}	Start-up time		V_{OUT} = 3 V, R_L = 30 Ω, C_{OUT} = 1 µF		600		µs
$V_{EN(HI)}$	EN pin high (enabled)			1.7		V_{IN}	V
$V_{EN(LO)}$	EN pin low (shutdown)			0		0.5	V
$I_{EN(HI)}$	EN pin current (enabled)		V_{EN} = 5.5 V		20		nA
T_{sd}	Thermal shutdown temperature		Shutdown, temperature increasing		160		°C
			Reset, temperature decreasing		140		
T_J	Operating junction temperature			–40		125	°C

(1) Minimum V_{IN} = V_{OUT} + V_{DO} or 2.2 V, whichever is greater.
(2) For $V_{OUT(nom)}$ < 1.6 V, when V_{IN} ≤ 1.6V, the output locks to V_{IN} and may result in an over-voltage condition on the output. To avoid this situation, disable the device before powering down V_{IN}.
(3) TPS73701 is tested at V_{OUT} = 1.2 V.
(4) Tolerance of external resistors not included in this specification.
(5) V_{DO} is not measured for fixed output versions with $V_{OUT(nom)}$ < 2.3 V because minimum V_{IN} = 2.2 V.
(6) Fixed-voltage versions only; refer to the *Application Information* section for more information.

Copyright © 2006–2019, Texas Instruments Incorporated

6.6 Typical Characteristics

For all voltage versions at T_J = 25°C, V_{IN} = $V_{OUT(nom)}$ + 1 V, I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted.

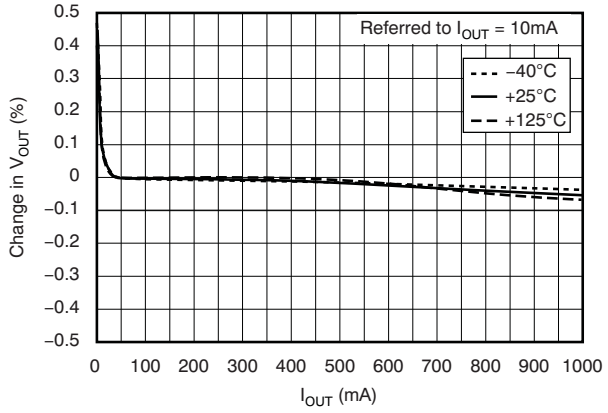


Figure 1. Load Regulation

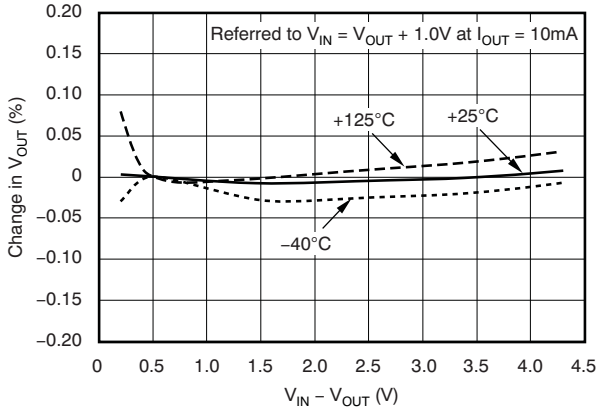


Figure 2. Line Regulation

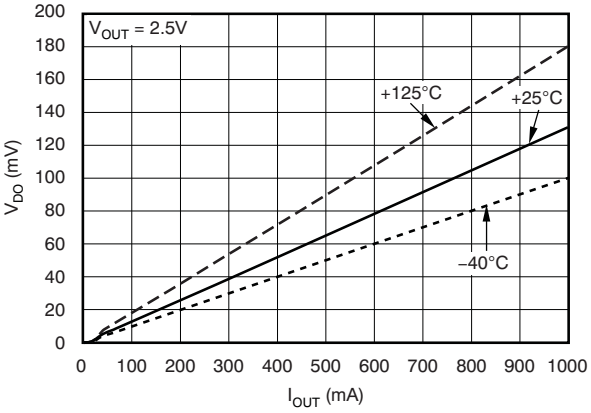


Figure 3. Dropout Voltage vs Output Current

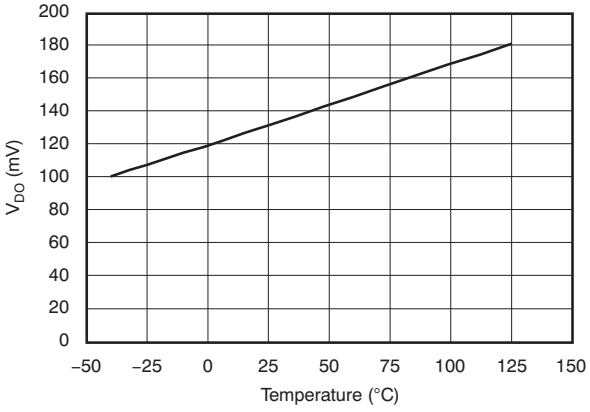


Figure 4. Dropout Voltage vs Temperature

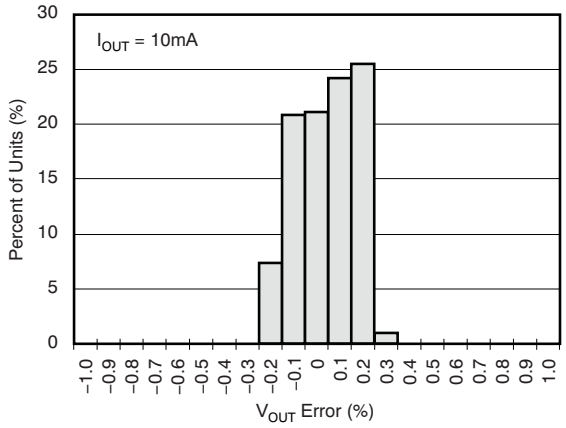


Figure 5. Output Voltage Histogram

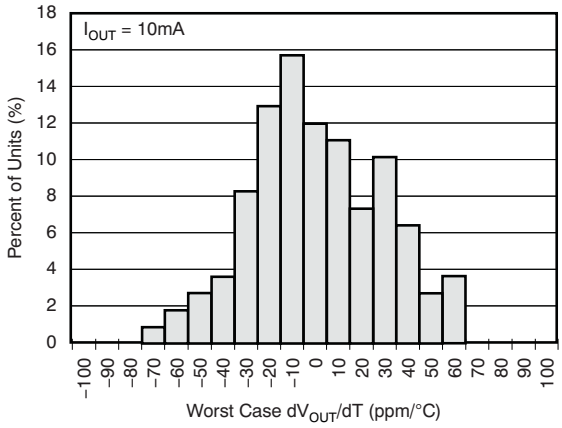


Figure 6. Output Voltage Drift Histogram

Copyright © 2006–2019, Texas Instruments Incorporated

Typical Characteristics (continued)

For all voltage versions at T_J = 25°C, V_{IN} = $V_{OUT(nom)}$ + 1 V, I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted.

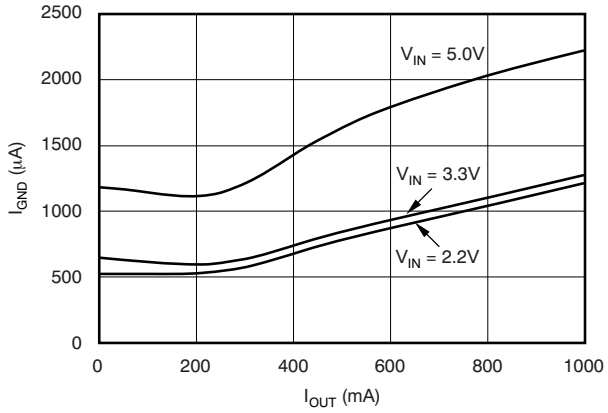


Figure 7. Ground Pin Current vs Output Current

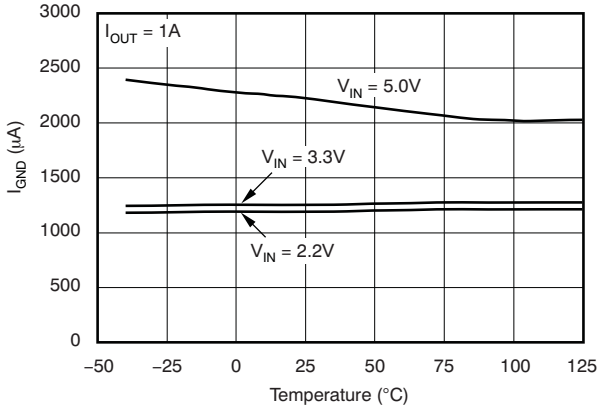


Figure 8. Ground Pin Current vs Temperature

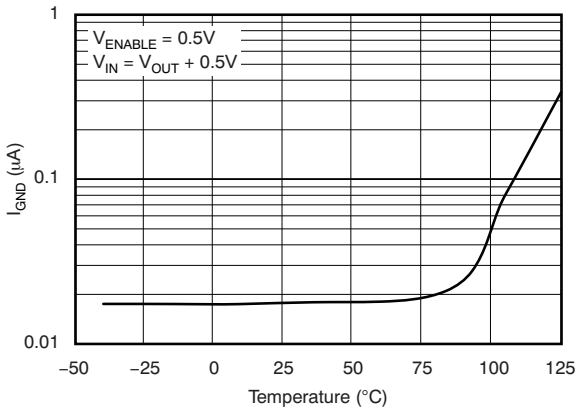


Figure 9. Ground Pin Current in Shutdown vs Temperature

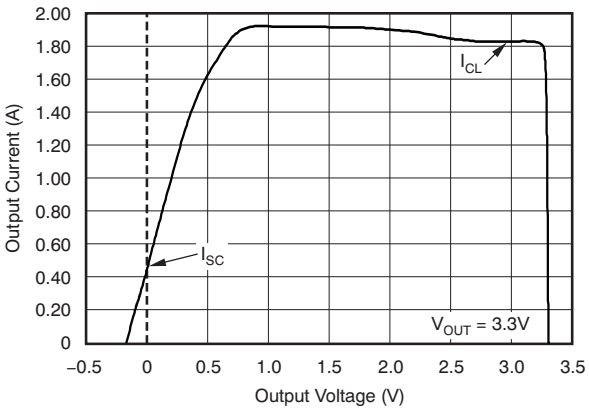


Figure 10. Current Limit vs V_{OUT} (Foldback)

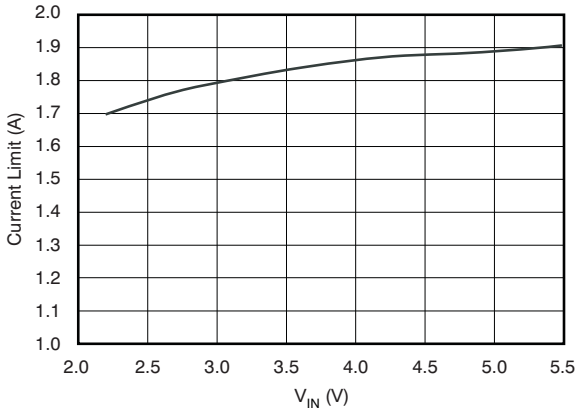


Figure 11. Current Limit vs V_{IN}

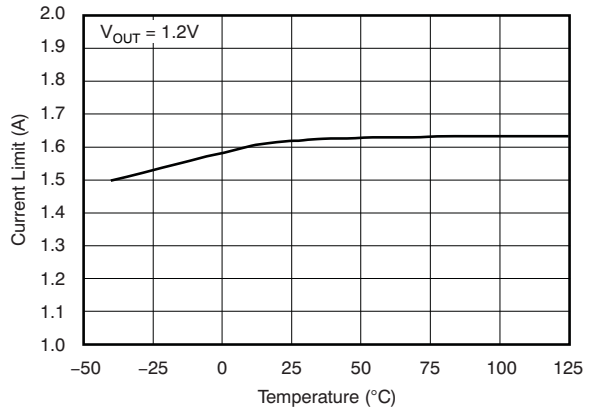


Figure 12. Current Limit vs Temperature

Copyright © 2006–2019, Texas Instruments Incorporated

Typical Characteristics (continued)

For all voltage versions at T_J = 25°C, V_{IN} = $V_{OUT(nom)}$ + 1 V, I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted.

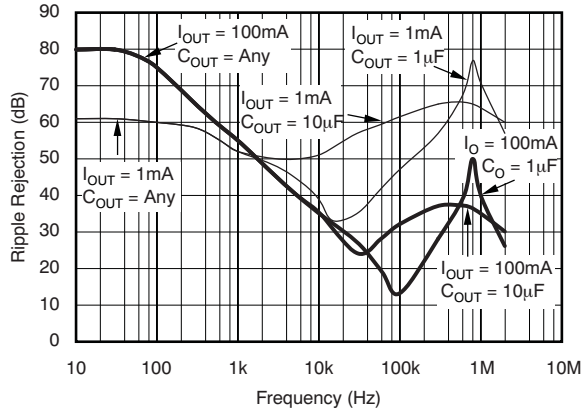


Figure 13. PSRR (Ripple Rejection) vs Frequency

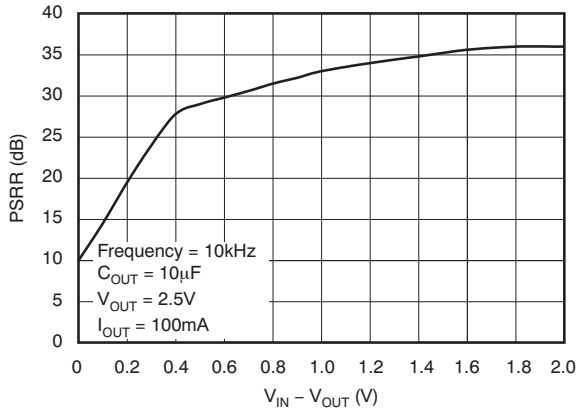


Figure 14. PSRR (Ripple Rejection) vs (V_{IN} – V_{OUT})

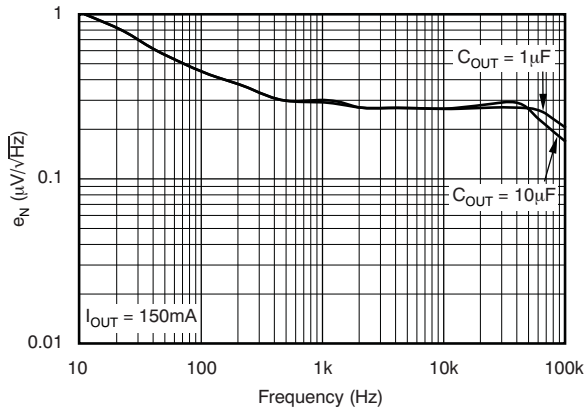


Figure 15. Noise Spectral Density

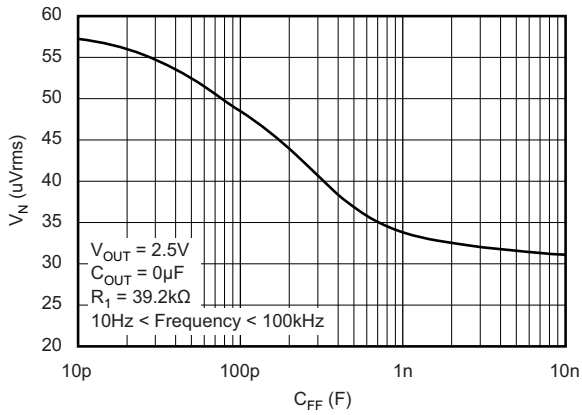


Figure 16. TPS73701 RMS Noise Voltage vs C_{FB}

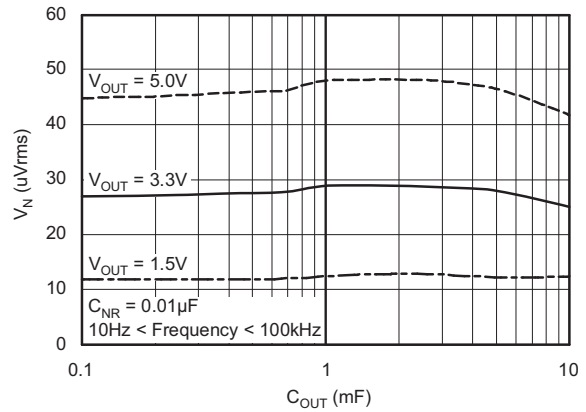


Figure 17. RMS Noise Voltage vs C_{OUT}

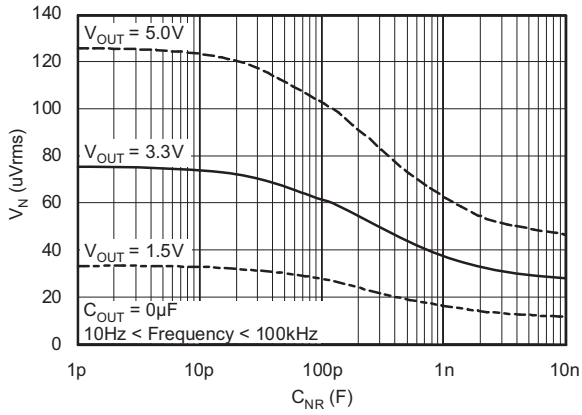


Figure 18. RMS Noise Voltage vs C_{NR}

Copyright © 2006–2019, Texas Instruments Incorporated

Typical Characteristics (continued)

For all voltage versions at T_J = 25°C, V_{IN} = $V_{OUT(nom)}$ + 1 V, I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted.

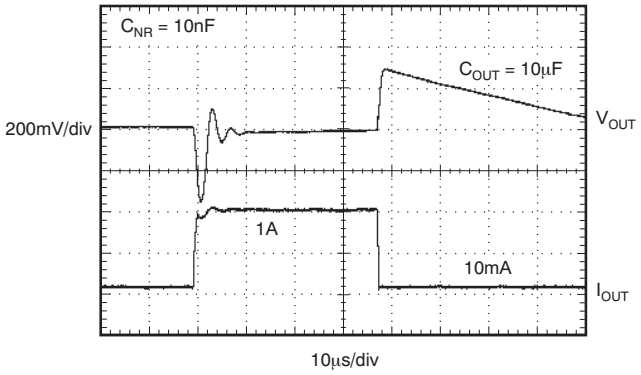


Figure 19. TPS73733 Load Transient Response

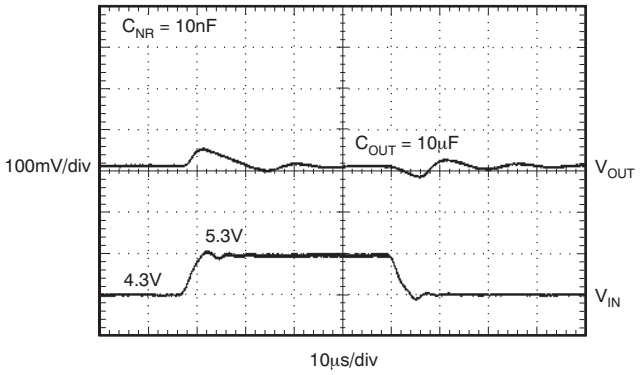


Figure 20. TPS73733 Line Transient Response

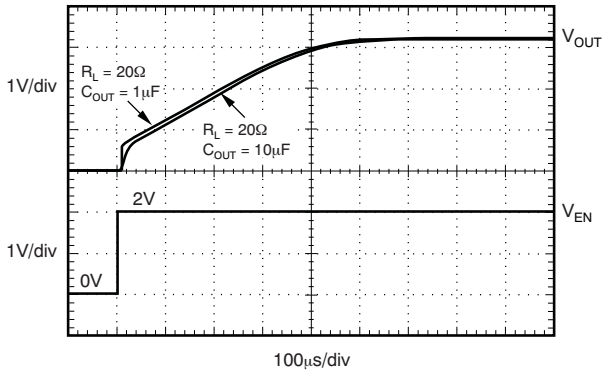


Figure 21. TPS73701 Turnon Response

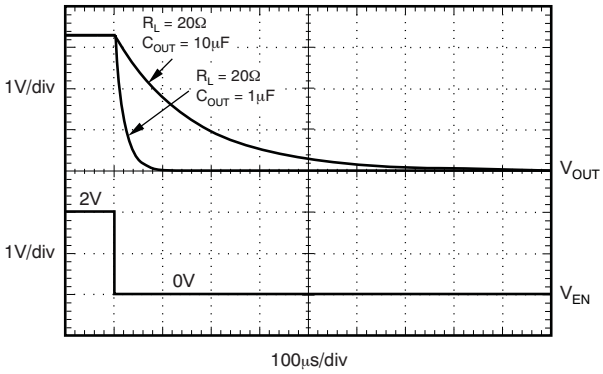


Figure 22. TPS73701 Turnoff Response

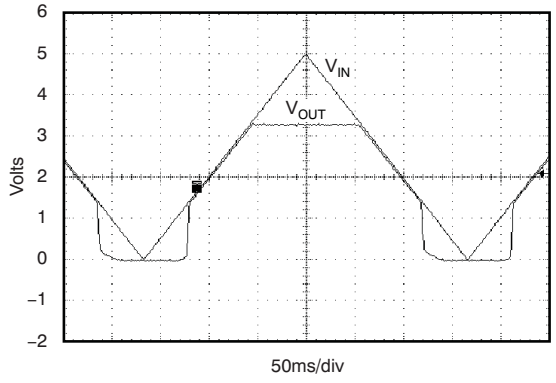


Figure 23. TPS73701, V_{OUT} = 3.3-V Power Up and Power Down

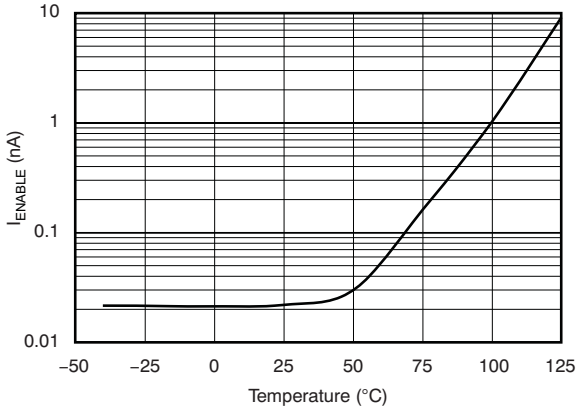


Figure 24. I_{EN} vs Temperature

Typical Characteristics (continued)

For all voltage versions at T_J = 25°C, V_{IN} = $V_{OUT(nom)}$ + 1 V, I_{OUT} = 10 mA, V_{EN} = 2.2 V, and C_{OUT} = 2.2 µF, unless otherwise noted.

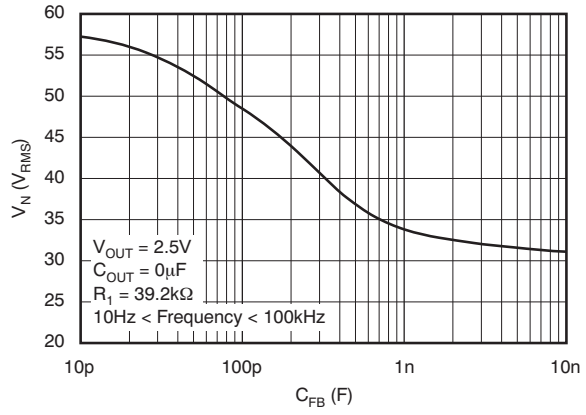


Figure 25. TPS73701 RMS Noise Voltage vs C_{FB}

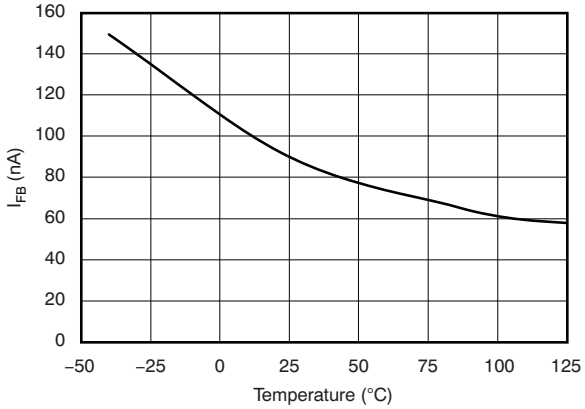


Figure 26. TPS73701 I_{FB} vs Temperature

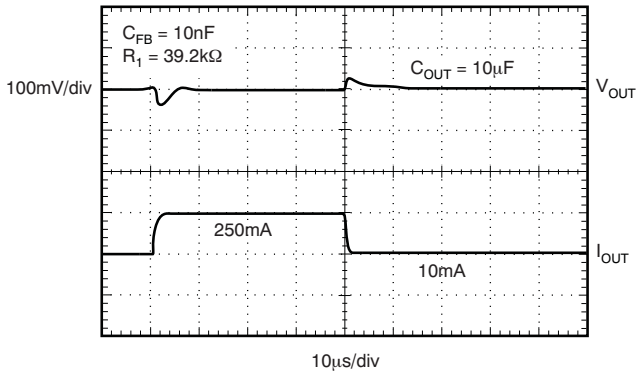


Figure 27. TPS73701 Load Transient, Adjustable Version

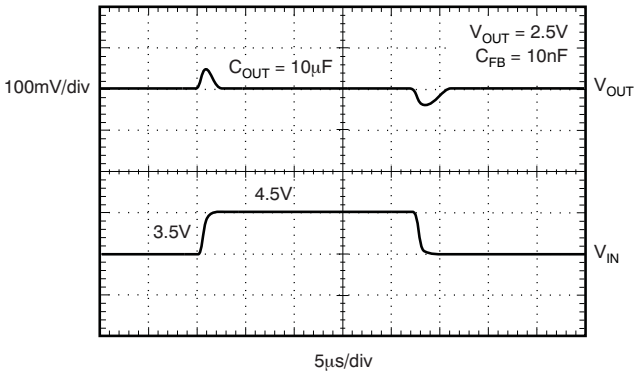


Figure 28. TPS73701 Line Transient, Adjustable Version

Copyright © 2006–2019, Texas Instruments Incorporated

7 Detailed Description

7.1 Overview

The TPS737xx belongs to a family of new generation LDO regulators that use an NMOS pass transistor to achieve ultralow dropout performance, reverse current blockage, and freedom from output capacitor constraints. These features combined with an enable input make the TPS737xx ideal for portable applications. This regulator family offers a wide selection of fixed-output voltage versions and an adjustable-output version. All versions have thermal and overcurrent protection, including foldback current-limit.

7.2 Functional Block Diagrams

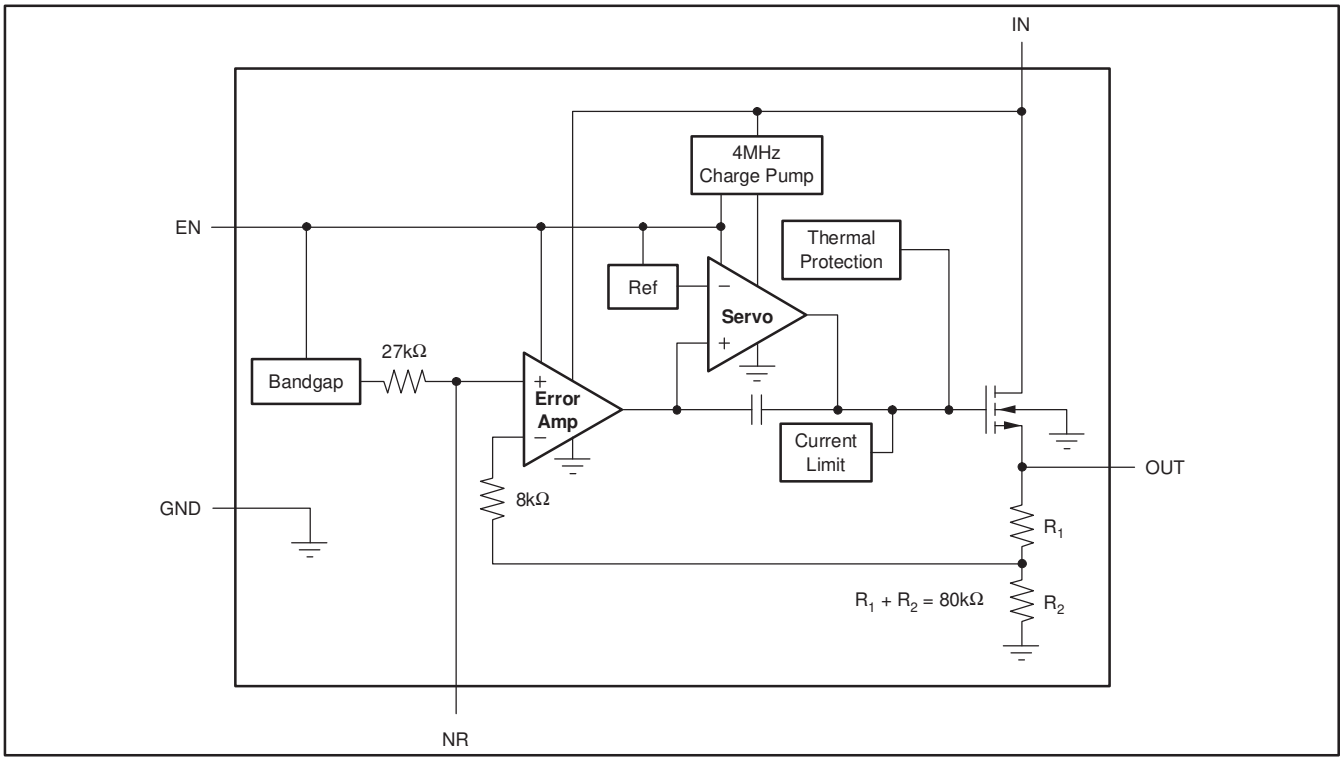
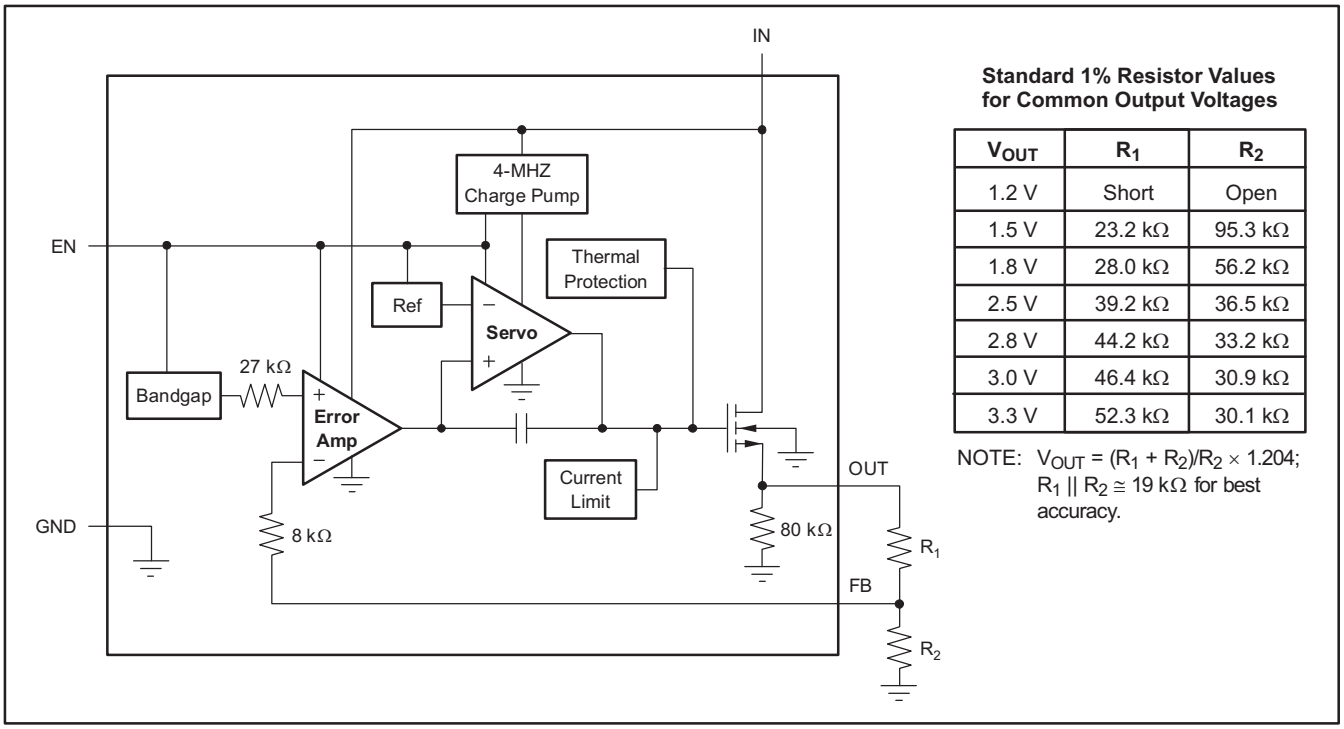


Figure 29. Fixed-Voltage Version

Copyright © 2006–2019, Texas Instruments Incorporated

Functional Block Diagrams (continued)



Standard 1% Resistor Values for Common Output Voltages

V_{OUT}	R_1	R_2
1.2 V	Short	Open
1.5 V	23.2 kΩ	95.3 kΩ
1.8 V	28.0 kΩ	56.2 kΩ
2.5 V	39.2 kΩ	36.5 kΩ
2.8 V	44.2 kΩ	33.2 kΩ
3.0 V	46.4 kΩ	30.9 kΩ
3.3 V	52.3 kΩ	30.1 kΩ

NOTE: $V_{OUT} = (R_1 + R_2)/R_2 \times 1.204$; $R_1 \parallel R_2 \cong 19\ k\Omega$ for best accuracy.

Figure 30. Adjustable-Voltage Version

7.3 Feature Description

7.3.1 Output Noise

A precision bandgap reference is used to generate the internal reference voltage, V_{ref}. This reference is the dominant noise source within the TPS737xx and it generates approximately 32 μV_{RMS} (10 Hz to 100 kHz) at the reference output (NR). The regulator control loop gains up the reference noise with the same gain as the reference voltage, so that the noise voltage of the regulator is approximately given by:

$$V_N = 32\mu V_{RMS} \times \frac{(R_1 + R_2)}{R_2} = 32\mu V_{RMS} \times \frac{V_{OUT}}{V_{REF}} \quad (1)$$

Because the value of V_R is 1.2 V, this relationship reduces to:

$$V_N(\mu V_{RMS}) = 27\left(\frac{\mu V_{RMS}}{V}\right) \times V_{OUT}(V) \quad (2)$$

for the case of no C_{NR}.

An internal 27-kΩ resistor in series with the noise reduction pin (NR) forms a low-pass filter for the voltage reference when an external noise reduction capacitor, C_{NR}, is connected from NR to ground. For C_{NR} = 10 nF, the total noise in the 10-Hz to 100-kHz bandwidth is reduced by a factor of approximately 3.2, giving the approximate relationship:

$$V_N(\mu V_{RMS}) = 8.5\left(\frac{\mu V_{RMS}}{V}\right) \times V_{OUT}(V) \quad (3)$$

for C_{NR} = 10 nF.

This noise reduction effect is shown as *RMS Noise Voltage vs C_{NR}* in the *Typical Characteristics* section.

Copyright © 2006–2019, Texas Instruments Incorporated

Feature Description (continued)

The TPS73701 adjustable version does not have the NR pin available. However, connecting a feedback capacitor, C_{FB}, from the output to the feedback pin (FB) reduces output noise and improve load transient performance. This capacitor should be limited to 0.1 µF.

The TPS737xx uses an internal charge pump to develop an internal supply voltage sufficient to drive the gate of the NMOS pass element above V_{OUT}. The charge pump generates approximately 250 µV of switching noise at approximately 4 MHz; however, charge-pump noise contribution is negligible at the output of the regulator for most values of I_{OUT} and C_{OUT}.

7.3.2 Internal Current Limit

The TPS737xx internal current limit helps protect the regulator during fault conditions. Foldback current-limit helps to protect the regulator from damage during output short-circuit conditions by reducing current-limit when V_{OUT} drops below 0.5 V. See Figure 10 in the *Typical Characteristics* section.

Note from Figure 10 that approximately –0.2 V of V_{OUT} results in a current-limit of 0 mA. Therefore, if OUT is forced below –0.2 V before EN goes high, the device may not start up. In applications that work with both a positive and negative voltage supply, the TPS737xx should be enabled first.

7.3.3 Enable Pin and Shutdown

The enable pin (EN) is active high and is compatible with standard TTL-CMOS levels. V_{EN} below 0.5 V (maximum) turns the regulator off and drops the GND pin current to approximately 10 nA. When EN is used to shutdown the regulator, all charge is removed from the pass transistor gate, and the output ramps back up to a regulated V_{OUT} (see Figure 21).

When shutdown capability is not required, EN can be connected to V_{IN}. However, the pass gate may not be discharged using this configuration, and the pass transistor may be left on (enhanced) for a significant time after V_{IN} has been removed. This scenario can result in reverse current flow (if the IN pin is low impedance) and faster ramp times upon power up. In addition, for V_{IN} ramp times slower than a few milliseconds, the output may overshoot upon power up.

Note that current limit foldback can prevent device start-up under some conditions. See the *Internal Current Limit* section for more information.

7.3.4 Reverse Current

The NMOS pass element of the TPS737xx provides inherent protection against current flow from the output of the regulator to the input when the gate of the pass device is pulled low. To ensure that all charge is removed from the gate of the pass element, the EN pin must be driven low before the input voltage is removed. If the EN pin is not driven low, the pass element may be left on because of stored charge on the gate.

After the EN pin is driven low, no bias voltage is needed on any pin for reverse current blocking. Reverse current is specified as the current flowing out of the IN pin because of voltage applied on the OUT pin. There is additional current flowing into the OUT pin as a result of the 80-kΩ internal resistor divider to ground (see Figure 29 and Figure 30).

For the TPS73701, reverse current may flow when V_{FB} is more than 1.0 V above V_{IN}.

7.4 Device Functional Modes

Driving the EN pin over 1.7 V turns on the regulator. Driving the EN pin below 0.5 V causes the regulator to enter shutdown mode. In shutdown, the current consumption of the device is reduced to 20 nA, typically.

Copyright © 2006–2019, Texas Instruments Incorporated

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPS737xx family of LDO regulators use an NMOS pass transistor to achieve ultra-low-dropout performance, reverse current blockage, and freedom from output capacitor constraints. These features, combined with low noise and an enable input, make the TPS737xx ideal for portable applications. This regulator family offers a wide selection of fixed-output voltage versions and an adjustable-output version. All versions have thermal and overcurrent protection, including foldback current-limit.

8.2 Typical Application

Figure 31 shows the basic circuit connections for the fixed-voltage models. Figure 32 gives the connections for the adjustable output version (TPS73701).

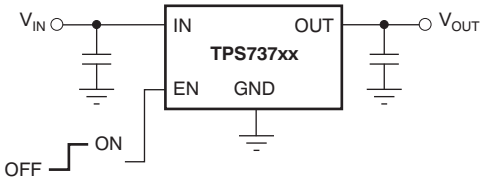


Figure 31. Typical Application Circuit for Fixed-Voltage Versions

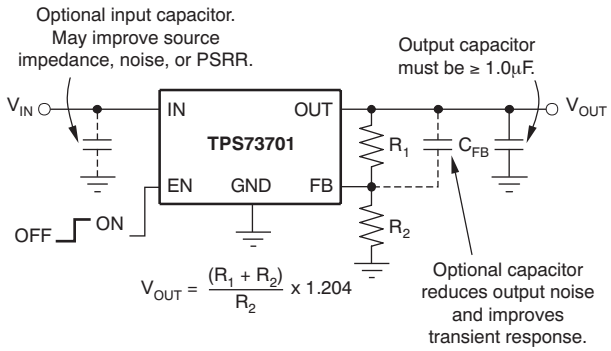


Figure 32. Typical Application Circuit for Adjustable-Voltage Version

8.2.1 Design Requirements

R_1 and R_2 can be calculated for any output voltage using the formula shown in Figure 32. Sample resistor values for common output voltages are shown in Figure 30.

For best accuracy, make the parallel combination of R_1 and R_2 approximately equal to 19 kΩ. This 19 kΩ, in addition to the internal 8-kΩ resistor, presents the same impedance to the error amp as the 27-kΩ bandgap reference output. This impedance helps compensate for leakages into the error amp terminals.

8.2.2 Detailed Design Procedure

Provide an input supply with adequate headroom to account for dropout and output current to compensate for the GND terminal current and to power the load. Further, select adequate input and output capacitors as discussed in *Input and Output Capacitor Requirements*.

Copyright © 2006–2019, Texas Instruments Incorporated

Typical Application (continued)

8.2.2.1 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability if input impedance is very low, it is good analog design practice to connect a 0.1-μF to 1-μF low equivalent series resistance (ESR) capacitor across the input supply near the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated or the device is located several inches from the power source.

The TPS737xx requires a 1-μF output capacitor for stability. It is designed to be stable for all available types and values of capacitors. In applications where multiple low-ESR capacitors are in parallel, ringing may occur when the product of C_{OUT} and total ESR drops below 50 nF. Total ESR includes all parasitic resistances, including capacitor ESR and board, socket, and solder joint resistance. In most applications, the sum of capacitor ESR and trace resistance meets this requirement.

8.2.2.2 Dropout Voltage

The TPS737xx uses an NMOS pass transistor to achieve extremely low dropout. When (V_{IN} – V_{OUT}) is less than the dropout voltage (V_{DO}), the NMOS pass device is in its linear region of operation and the input-to-output resistance is the $R_{DS(on)}$ of the NMOS pass element.

For large step changes in load current, the TPS737xx requires a larger voltage drop from V_{IN} to V_{OUT} to avoid degraded transient response. The boundary of this transient dropout region is approximately twice the DC dropout. Values of (V_{IN} – V_{OUT}) above this line ensure normal transient response.

Operating in the transient dropout region can cause an increase in recovery time. The time required to recover from a load transient is a function of the magnitude of the change in load current rate, the rate of change in load current, and the available headroom (V_{IN}-to-V_{OUT} voltage drop). Under worst-case conditions [full-scale instantaneous load change with (V_{IN} – V_{OUT}) close to DC dropout levels], the TPS737xx can take a couple of hundred microseconds to return to the specified regulation accuracy.

8.2.2.3 Transient Response

The low open-loop output impedance provided by the NMOS pass element in a voltage follower configuration allows operation without a 1-μF output capacitor. As with any regulator, the addition of additional capacitance from the OUT pin to ground reduces undershoot magnitude but increases its duration. In the adjustable version, the addition of a capacitor, C_{FB}, from the OUT pin to the FB pin will also improve the transient response.

The TPS737xx does not have active pulldown when the output is over-voltage. This architecture allows applications that connect higher voltage sources, such as alternate power supplies, to the output. This architecture also results in an output overshoot of several percent if the load current quickly drops to zero when a capacitor is connected to the output. The duration of overshoot can be reduced by adding a load resistor. The overshoot decays at a rate determined by output capacitor C_{OUT} and the internal/external load resistance. The rate of decay is given by:

(Fixed voltage version)

$$\frac{dV}{dT} = \frac{V_{OUT}}{C_{OUT} \times 80k\Omega \,||\, R_{LOAD}} \quad (4)$$

(Adjustable voltage version)

$$\frac{dV}{dT} = \frac{V_{OUT}}{C_{OUT} \times 80k\Omega \,||\, (R_1 + R_2) \,||\, R_{LOAD}} \quad (5)$$

Copyright © 2006–2019, Texas Instruments Incorporated

Typical Application (continued)

8.2.3 Application Curves

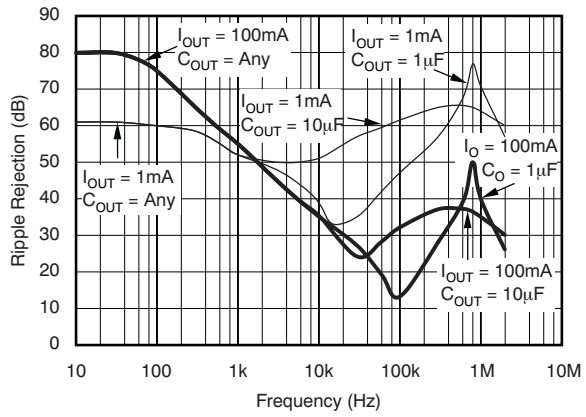


Figure 33. PSRR (Ripple Rejection) vs Frequency

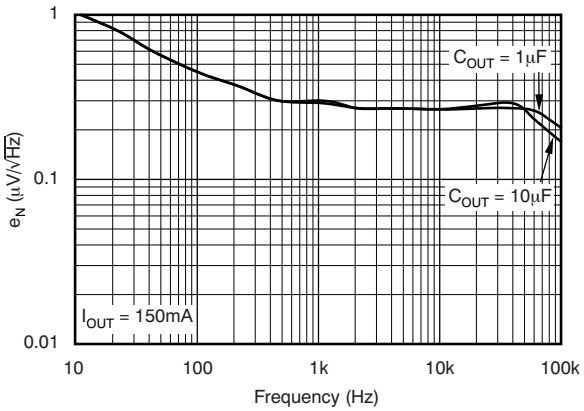


Figure 34. Noise Spectral Density

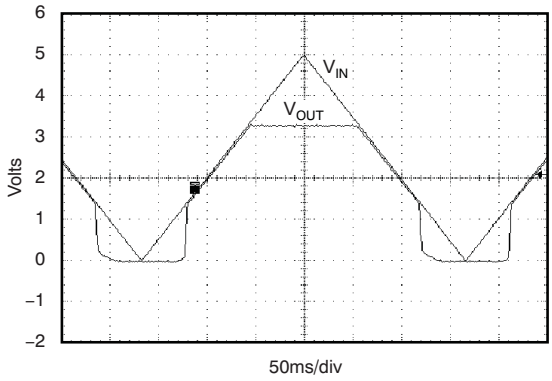


Figure 35. TPS73701, V_{OUT} = 3.3-V Power Up and Power Down

8.3 What To Do and What Not To Do

Place at least one 1-μF ceramic capacitor as close as possible to the OUT terminal of the regulator.

Do not place the output capacitor more than 10-mm away from the regulator.

Connect a 1-μF low equivalent series resistance (ESR) capacitor across the IN terminal and GND input of the regulator for improved transient performance.

Do not exceed the absolute maximum ratings.

9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range between 2.2 V and 5.5 V. The input voltage range provides adequate headroom in order for the device to have a regulated output. This input supply must be well regulated. If the input supply is noisy, additional input capacitors with low ESR help improve the output noise performance.

Copyright © 2006–2019, Texas Instruments Incorporated

10 Layout

10.1 Layout Guidelines

To improve AC performance such as PSRR, output noise, and transient response, TI recommends designing the printed-circuit-board (PCB) with separate ground planes for V_{IN} and V_{OUT}, with each ground plane connected only at the GND pin of the device. In addition, the ground connection for the bypass capacitor should connect directly to the GND pin of the device.

10.1.1 Power Dissipation

Knowing the device power dissipation and proper sizing of the thermal plane that is connected to the tab or pad is critical to avoiding thermal shutdown and ensuring reliable operation.

Power dissipation of the device depends on input voltage and load conditions and can be calculated using Equation 6:

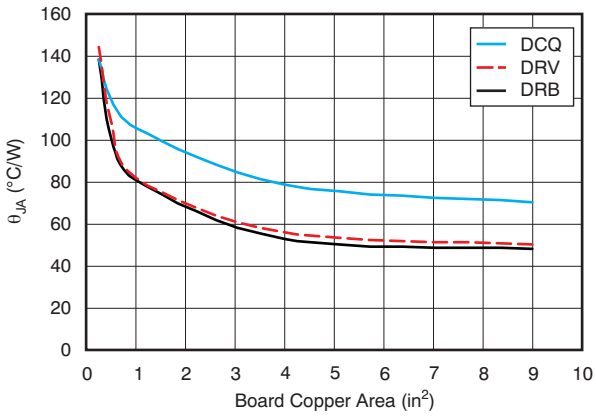
$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (6)$$

Power dissipation can be minimized and greater efficiency can be achieved by using the lowest possible input voltage necessary to achieve the required output voltage regulation.

On both SON (DRB) and SON (DRV) packages, the primary conduction path for heat is through the exposed pad to the printed circuit board (PCB). The pad can be connected to ground or be left floating; however, it should be attached to an appropriate amount of copper PCB area to ensure the device does not overheat. On the SOT-223 (DCQ) package, the primary conduction path for heat is through the tab to the PCB. That tab should be connected to ground. The maximum junction-to-ambient thermal resistance depends on the maximum ambient temperature, maximum device junction temperature, and power dissipation of the device and can be calculated using Equation 7:

$$R_{\theta JA} = \frac{(+125°C - T_A)}{P_D} \quad (7)$$

Knowing the maximum $R_{\theta JA}$, the minimum amount of PCB copper area needed for appropriate heatsinking can be estimated using Figure 36.



Note: θ_{JA} value at board size of 9 in^2 (that is, 3 in × 3 in) is a JEDEC standard.

Figure 36. θ_{JA} vs Board Size

Figure 36 shows the variation of θ_{JA} as a function of ground plane copper area in the board. It is intended only as a guideline to demonstrate the effects of heat spreading in the ground plane and should not be used to estimate actual thermal performance in real application environments.

NOTE

When the device is mounted on an application PCB, TI strongly recommends using Ψ_{JT} and Ψ_{JB}, as explained in the section.

Copyright © 2006–2019, Texas Instruments Incorporated

Layout Guidelines (continued)

10.1.2 Thermal Protection

Thermal protection disables the output when the junction temperature rises to approximately 160°C, allowing the device to cool. When the junction temperature cools to approximately 140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, protecting it from damage due to overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature should be limited to 125°C maximum. To estimate the margin of safety in a complete design (including heatsink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection should trigger at least 35°C above the maximum expected ambient condition of your application. This produces a worst-case junction temperature of 125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS737xx has been designed to protect against overload conditions. It was not intended to replace proper heatsinking. Continuously running the TPS737xx into thermal shutdown degrades device reliability.

10.1.3 Estimating Junction Temperature

Using the thermal metrics Ψ_{JT} and Ψ_{JB}, as shown in the *Thermal Information* table, the junction temperature can be estimated with corresponding formulas (given in Equation 8). For backward compatibility, an older $\theta_{JC,Top}$ parameter is listed as well.

$$\Psi_{JT}: \quad T_J = T_T + \Psi_{JT} \bullet P_D$$
$$\Psi_{JB}: \quad T_J = T_B + \Psi_{JB} \bullet P_D \tag{8}$$

Where P_D is the power dissipation shown by Equation 6, T_T is the temperature at the center-top of the IC package, and T_B is the PCB temperature measured 1-mm away from the IC package *on the PCB surface* (as Figure 38 shows).

NOTE

Both T_T and T_B can be measured on actual application boards using a thermo-gun (an infrared thermometer).

For more information about measuring T_T and T_B, see the application note, *Using New Thermal Metrics* (SBVA025), available for download at www.ti.com.

By looking at Figure 37, the new thermal metrics (Ψ_{JT} and Ψ_{JB}) have very little dependency on board size. That is, using Ψ_{JT} or Ψ_{JB} with Equation 8 is a good way to estimate T_J by simply measuring T_T or T_B, regardless of the application board size.

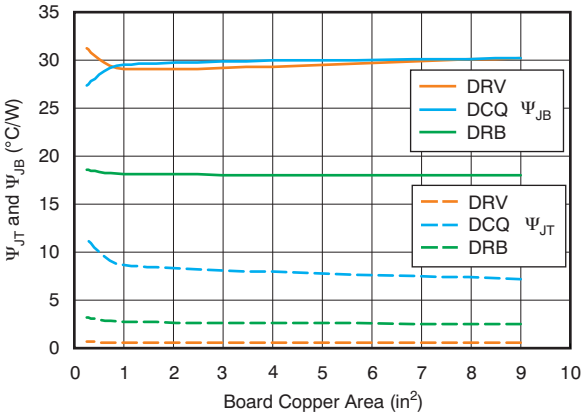
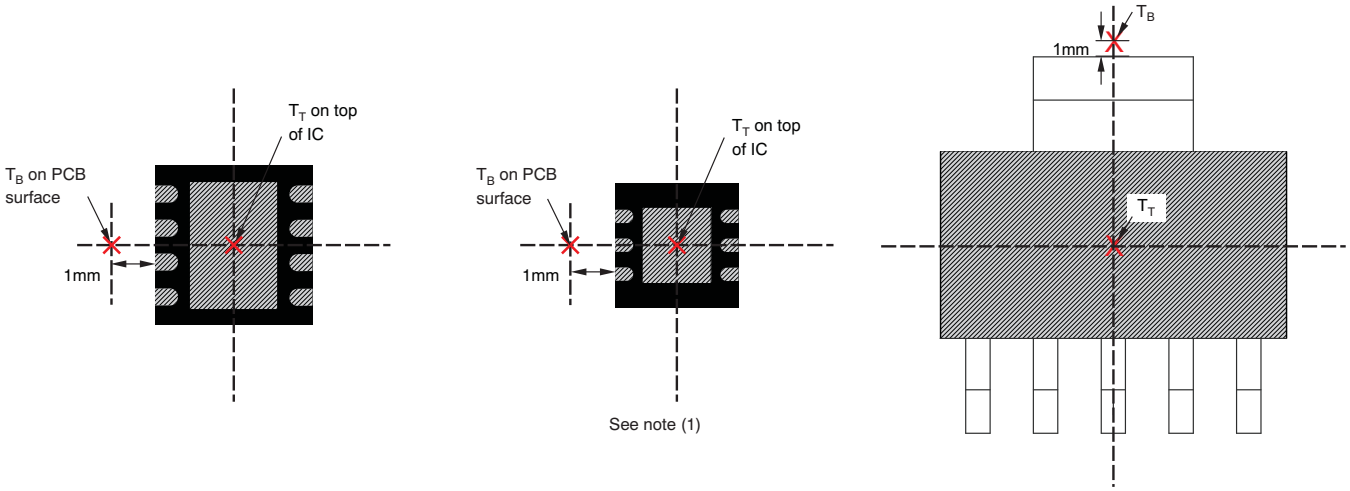


Figure 37. Ψ_{JT} and Ψ_{JB} vs Board Size

Copyright © 2006–2019, Texas Instruments Incorporated

Layout Guidelines (continued)

For a more detailed discussion of why TI does not recommend using $\theta_{JC(top)}$ to determine thermal characteristics, refer to application report, *Using New Thermal Metrics* (SBVA025), available for download at www.ti.com. For further information, refer to application report, *IC Package Thermal Metrics* (SPRA953), also available on the TI website.



(a) Example DRB (SON) Package Measurement (b) Example DRV (SON) Package Measurement (c) Example DCQ (SOT-223) Package Measurement

(1) Power dissipation may limit operating range. Check *Thermal Information* table.

Figure 38. Measuring Points for T_T and T_B

10.2 Layout Example

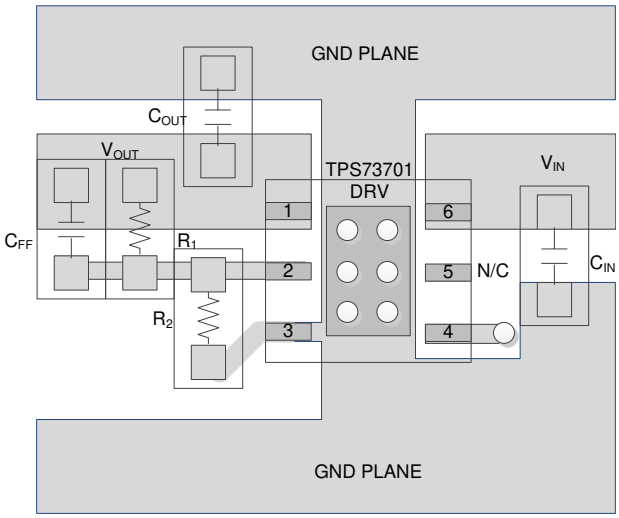


Figure 39. Layout Example

11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

11.1.1.1 评估模块

提供了一个评估模块 (EVM)，您可借此对使用 TPS737xx 的电路进行初始性能评估。TPS73701DRVEVM-529 评估模块（和相关的用户指南）可从德州仪器 (TI) 网站上的产品文件夹获取，也可直接从 TI 网上商店购买。

11.1.1.2 Spice 模型

分析模拟电路和系统的性能时，使用 SPICE 模型对电路性能进行计算机仿真非常有用。您可以从*工具和软件*下的产品文件夹中获取 TPS737 的 SPICE 模型。

11.1.2 器件命名规则

表 **1.** 订购信息 **(1)**

产品	V_{OUT} (1)
TPS737**xx yy yz**	**xx** 为标称输出电压（例如，25 = 2.5V，01 = 可调节 (2)）。
	yyy 为封装标识符。
	z 为封装数量。

(1) 有关最新的封装和订货信息，请参阅本文档末尾的封装选项附录，或访问 www.ti.com.cn 查看器件产品文件夹。
(2) 以固定电压 1.20V 运行时，将 FB 连接至 OUT。

11.2 文档支持

11.2.1 相关文档

- 德州仪器 (TI)，*《使用新的热度量指标》 应用报告*
- 德州仪器 (TI)，*《TPS73701DRVEVM-529 用户指南》*
- 德州仪器 (TI)，*《TMS320DM644x 电源参考设计》 应用报告*
- 德州仪器 (TI)，*《TPS73x01DRBEVM-518 用户指南》*

11.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com.cn 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.4 支持资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.5 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.6 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

版权 © 2006–2019, Texas Instruments Incorporated

11.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

版权 © 2006–2019, Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS73701DCQ	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73701	Samples
TPS73701DCQG4	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73701	Samples
TPS73701DCQR	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73701	Samples
TPS73701DCQRG4	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73701	Samples
TPS73701DRBR	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BZN	Samples
TPS73701DRBRG4	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BZN	Samples
TPS73701DRBT	ACTIVE	SON	DRB	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	BZN	Samples
TPS73701DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTN	Samples
TPS73701DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	QTN	Samples
TPS73718DCQ	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73718	Samples
TPS73718DCQG4	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73718	Samples
TPS73718DCQR	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73718	Samples
TPS73718DCQRG4	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73718	Samples
TPS73718DRBR	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RAL	Samples
TPS73718DRBT	ACTIVE	SON	DRB	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	RAL	Samples
TPS73725DCQ	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73725	Samples
TPS73725DCQR	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73725	Samples
TPS73725DCQRG4	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73725	Samples
TPS73730DRBR	ACTIVE	SON	DRB	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CVT	Samples
TPS73730DRBT	ACTIVE	SON	DRB	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CVT	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS73733DCQ	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73733	Samples
TPS73733DCQG4	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73733	Samples
TPS73733DCQR	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TPS73733	Samples
TPS73733DCQRG4	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS73733	Samples
TPS73733DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SIJ	Samples
TPS73733DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SIJ	Samples
TPS73734DCQ	ACTIVE	SOT-223	DCQ	6	78	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OCH	Samples
TPS73734DCQR	ACTIVE	SOT-223	DCQ	6	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OCH	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

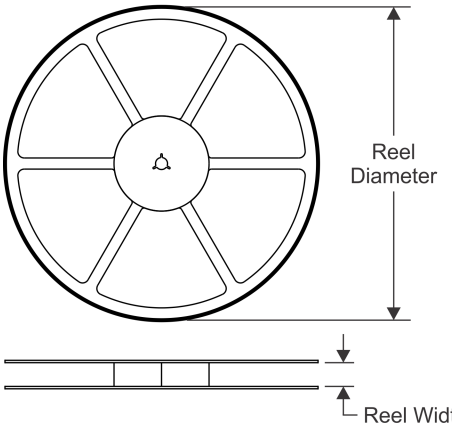
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

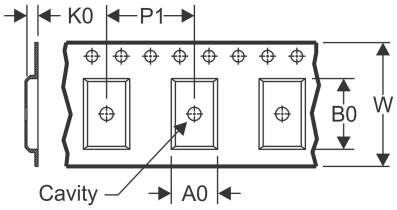
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

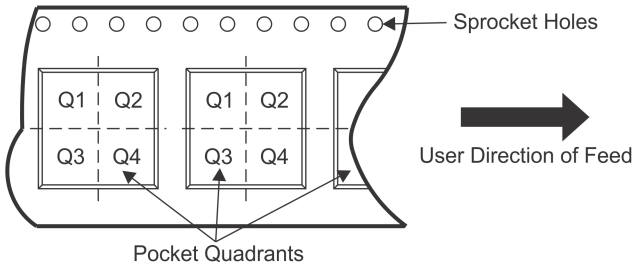


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

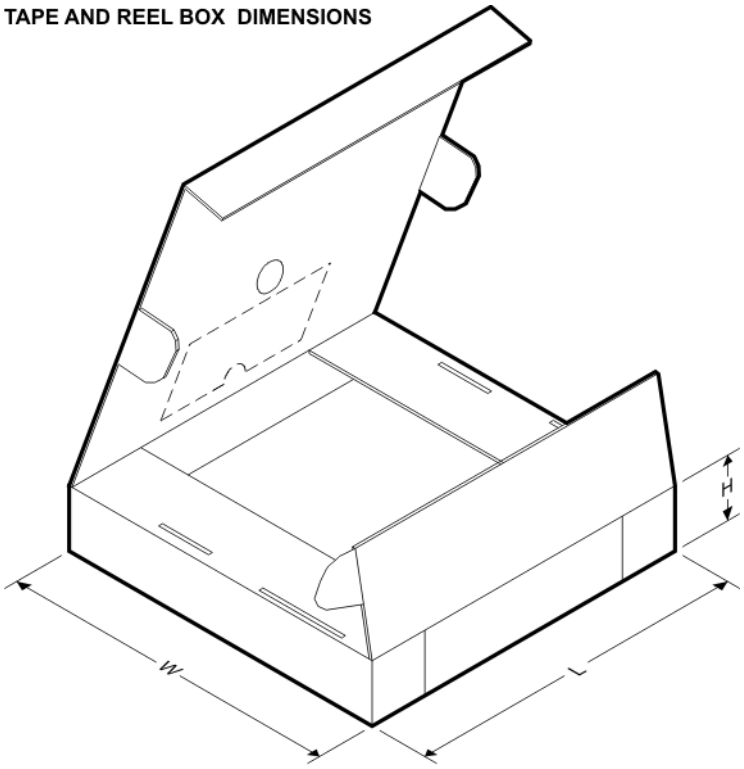


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS73701DCQR	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73701DCQRG4	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73701DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73701DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73701DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73701DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73701DRBT	SON	DRB	8	250	180.0	12.5	3.3	3.3	1.1	8.0	12.0	Q2
TPS73701DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73701DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73718DCQR	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73718DCQRG4	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73718DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73718DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73725DCQR	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73725DCQRG4	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73730DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73730DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS73733DCQR	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS73733DCQRG4	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3
TPS73733DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73733DRVT	WSON	DRV	6	250	180.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS73734DCQR	SOT-223	DCQ	6	2500	330.0	12.4	7.1	7.45	1.88	8.0	12.0	Q3

TAPE AND REEL BOX DIMENSIONS

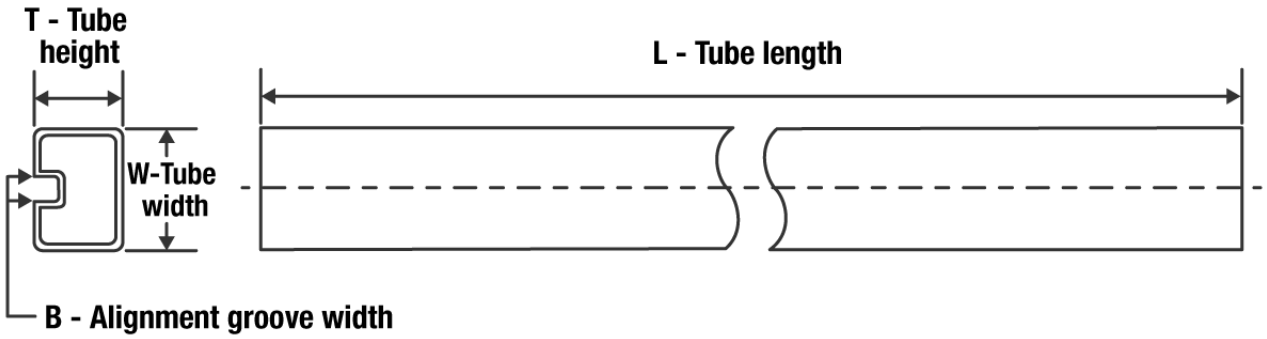


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS73701DCQR	SOT-223	DCQ	6	2500	853.0	449.0	35.0
TPS73701DCQRG4	SOT-223	DCQ	6	2500	346.0	346.0	29.0
TPS73701DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73701DRBR	SON	DRB	8	3000	338.0	355.0	50.0
TPS73701DRBR	SON	DRB	8	3000	552.0	367.0	36.0
TPS73701DRBT	SON	DRB	8	250	552.0	185.0	36.0
TPS73701DRBT	SON	DRB	8	250	338.0	355.0	50.0
TPS73701DRVR	WSON	DRV	6	3000	213.0	191.0	35.0
TPS73701DRVT	WSON	DRV	6	250	213.0	191.0	35.0
TPS73718DCQR	SOT-223	DCQ	6	2500	853.0	449.0	35.0
TPS73718DCQRG4	SOT-223	DCQ	6	2500	346.0	346.0	29.0
TPS73718DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73718DRBT	SON	DRB	8	250	210.0	185.0	35.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS73725DCQR	SOT-223	DCQ	6	2500	853.0	449.0	35.0
TPS73725DCQRG4	SOT-223	DCQ	6	2500	346.0	346.0	41.0
TPS73730DRBR	SON	DRB	8	3000	853.0	449.0	35.0
TPS73730DRBT	SON	DRB	8	250	210.0	185.0	35.0
TPS73733DCQR	SOT-223	DCQ	6	2500	853.0	449.0	35.0
TPS73733DCQRG4	SOT-223	DCQ	6	2500	346.0	346.0	41.0
TPS73733DRVR	WSON	DRV	6	3000	213.0	191.0	35.0
TPS73733DRVT	WSON	DRV	6	250	213.0	191.0	35.0
TPS73734DCQR	SOT-223	DCQ	6	2500	346.0	346.0	41.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS73701DCQ	DCQ	SOT-223	6	78	543	8.6	3606.8	2.67
TPS73701DCQG4	DCQ	SOT-223	6	78	532.13	8.63	3.6	3.68
TPS73701DRBR	DRB	VSON	8	3000	381	4.83	2286	0
TPS73701DRBRG4	DRB	VSON	8	3000	381	4.83	2286	0
TPS73701DRBT	DRB	VSON	8	250	381	4.83	2286	0
TPS73718DCQ	DCQ	SOT-223	6	78	543	8.6	3606.8	2.67
TPS73718DCQG4	DCQ	SOT-223	6	78	532.13	8.63	3.6	3.68
TPS73725DCQ	DCQ	SOT-223	6	78	532.13	8.63	3.6	3.68
TPS73733DCQ	DCQ	SOT-223	6	78	543	8.6	3606.8	2.67
TPS73733DCQG4	DCQ	SOT-223	6	78	532.13	8.63	3.6	3.68
TPS73734DCQ	DCQ	SOT-223	6	78	532.13	8.63	3.6	3.68

GENERIC PACKAGE VIEW

DRB 8 VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

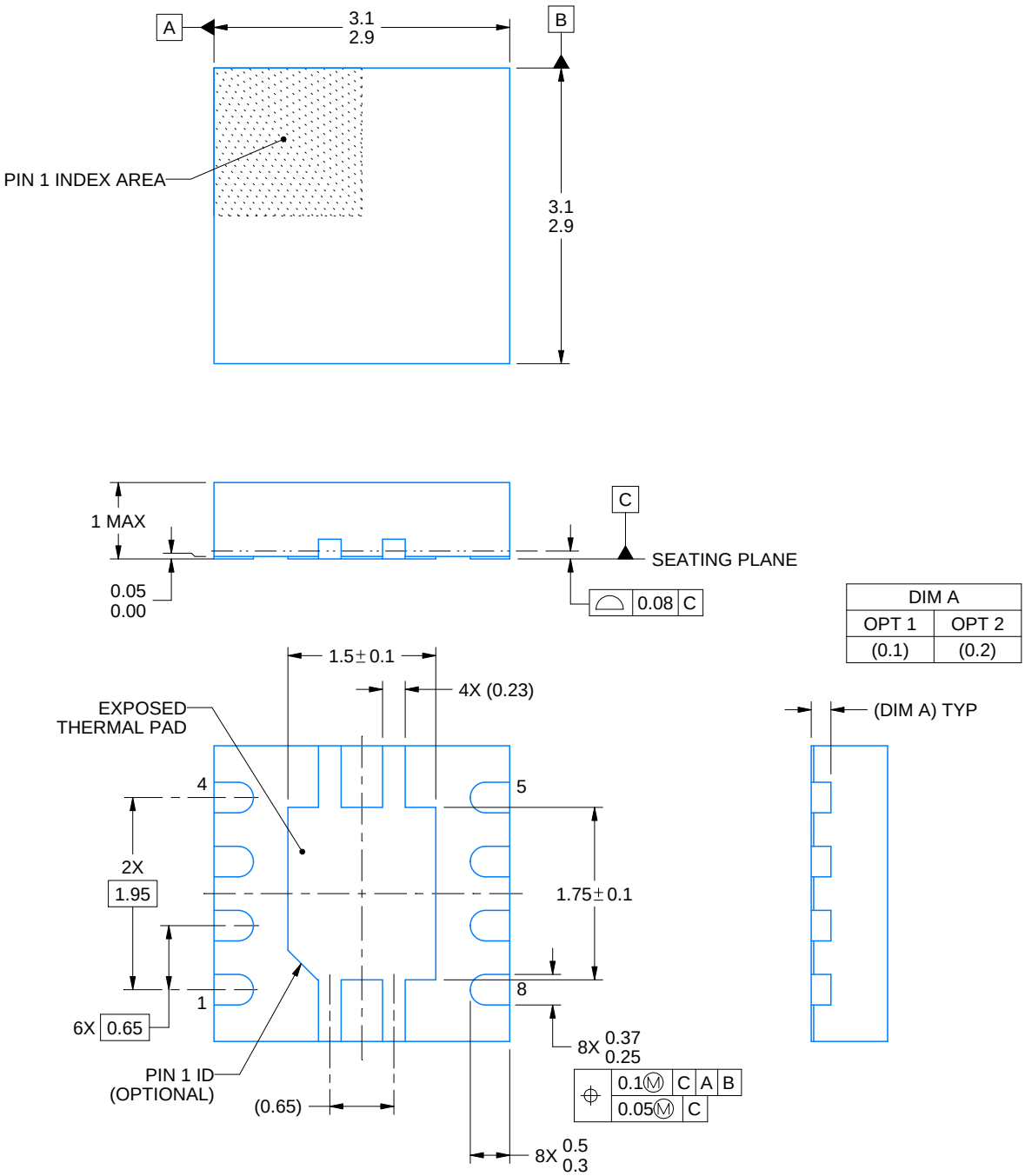
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

DRB0008A

PACKAGE OUTLINE

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

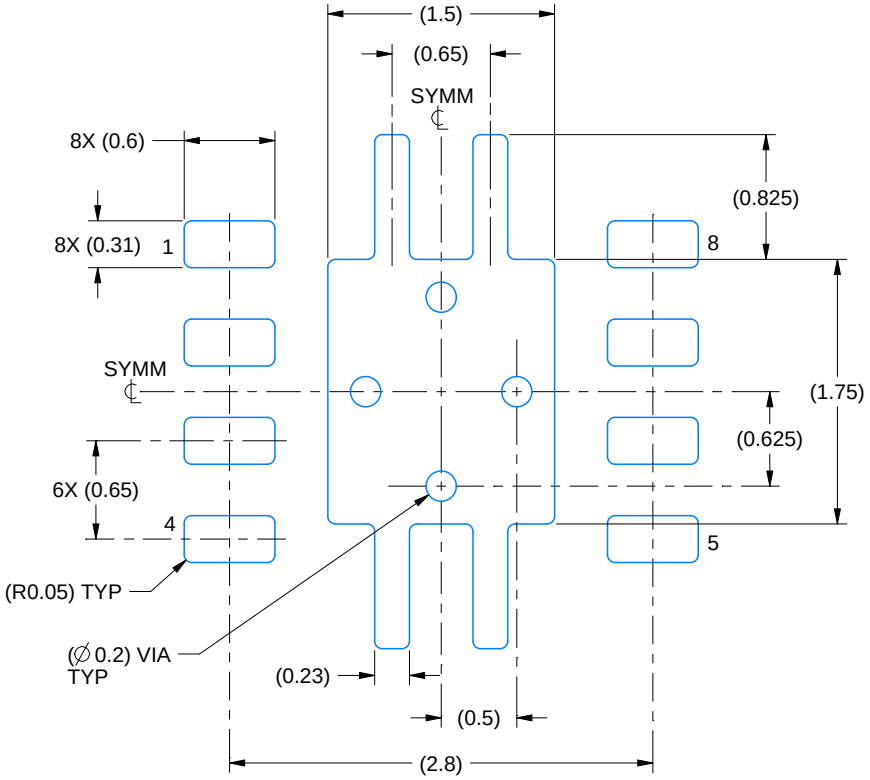
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

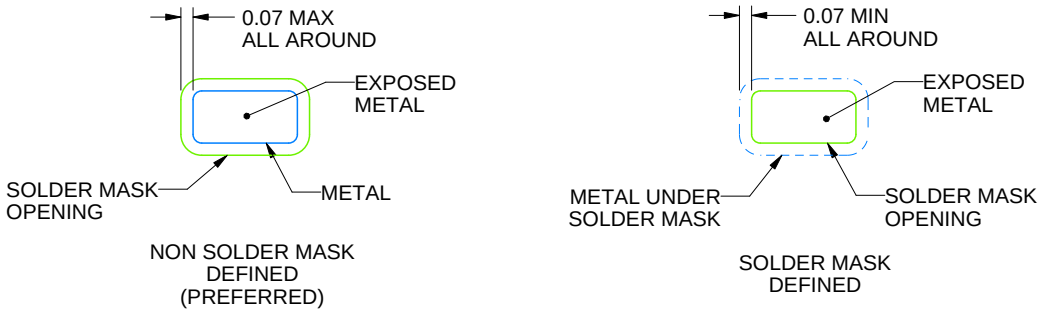
DRB0008A

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X

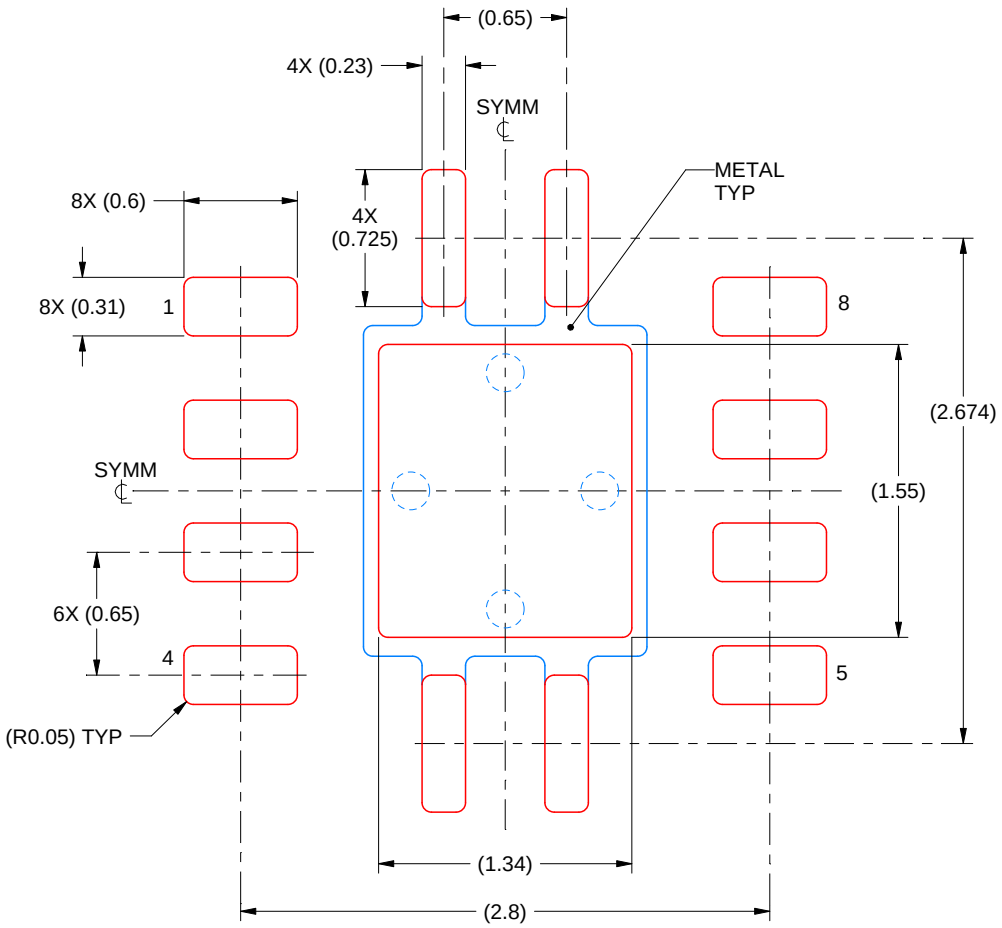


SOLDER MASK DETAILS

4218875/A 01/2018

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
84% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218875/A 01/2018

NOTES: (continued)

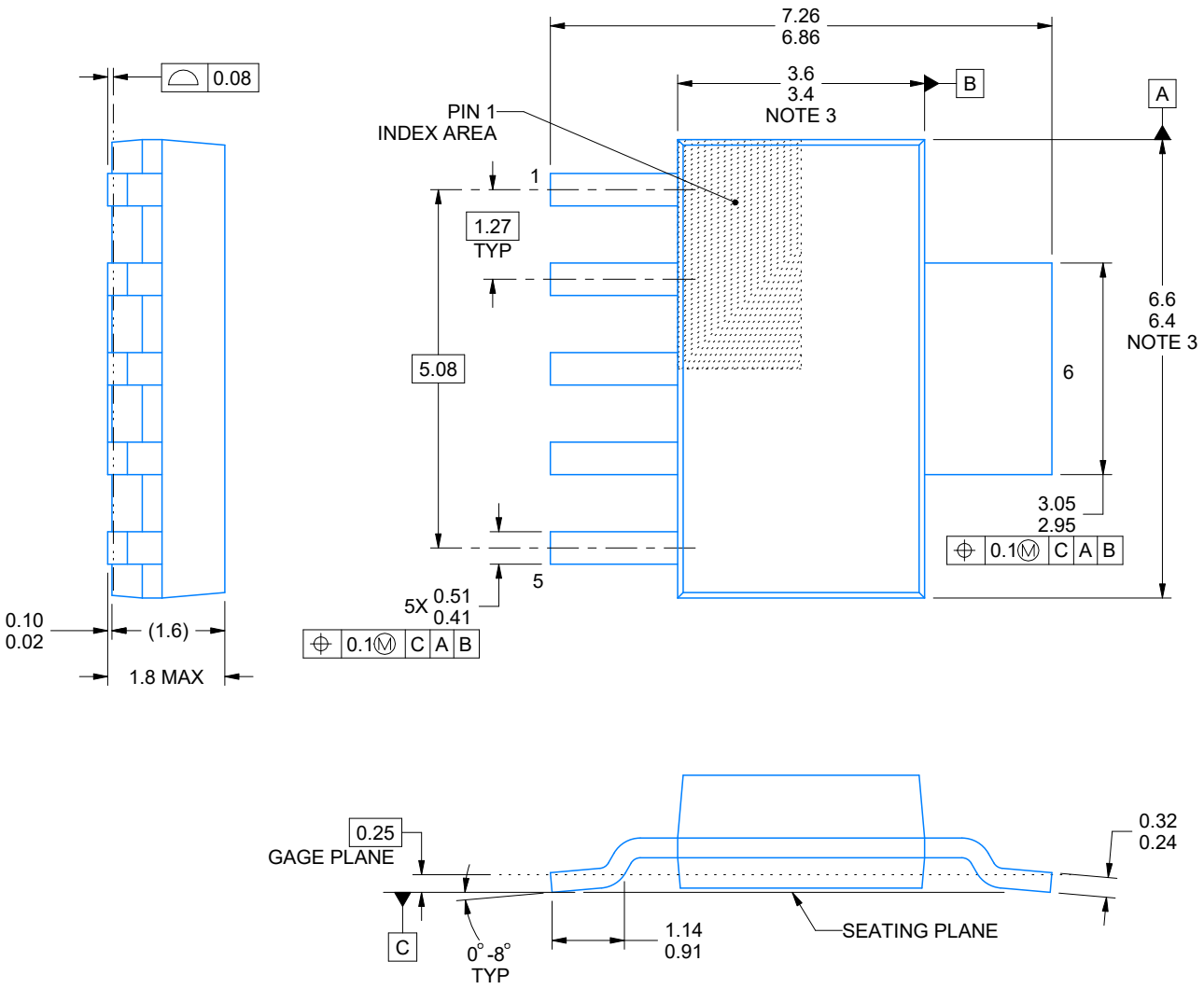
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

DCQ0006A

SOT - 1.8 mm max height

PLASTIC SMALL OUTLINE



4214845/C 11/2021

NOTES:

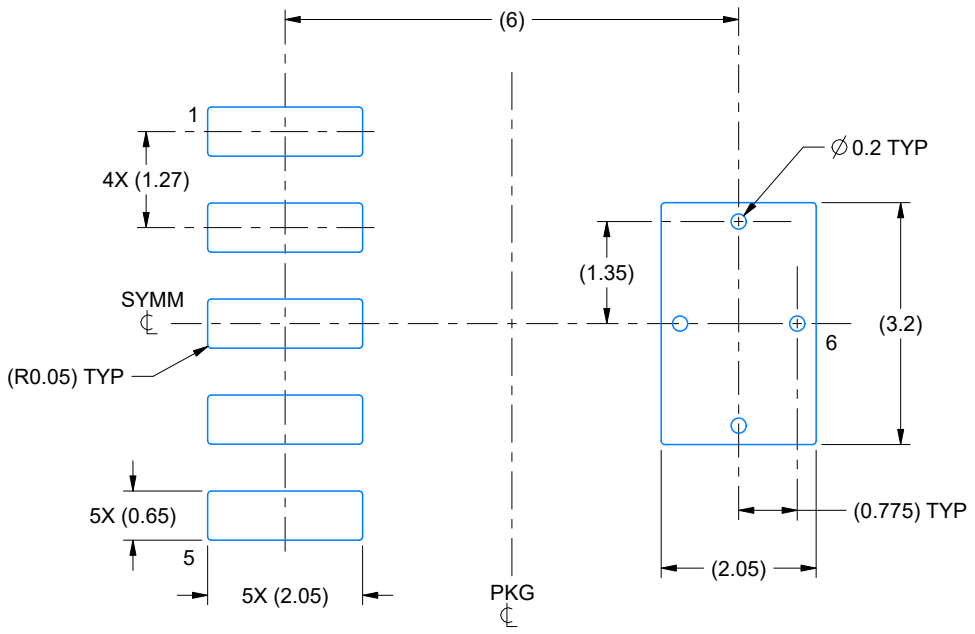
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

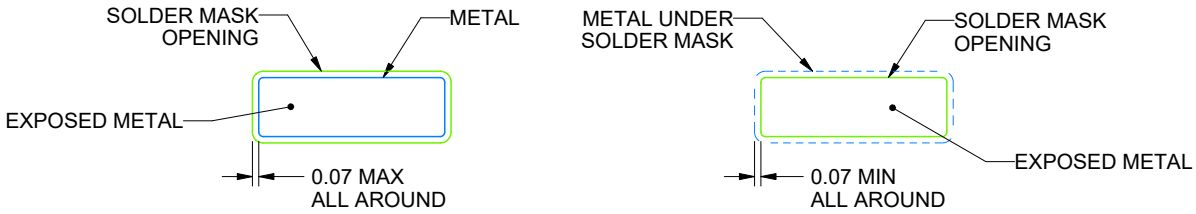
DCQ0006A

SOT - 1.8 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

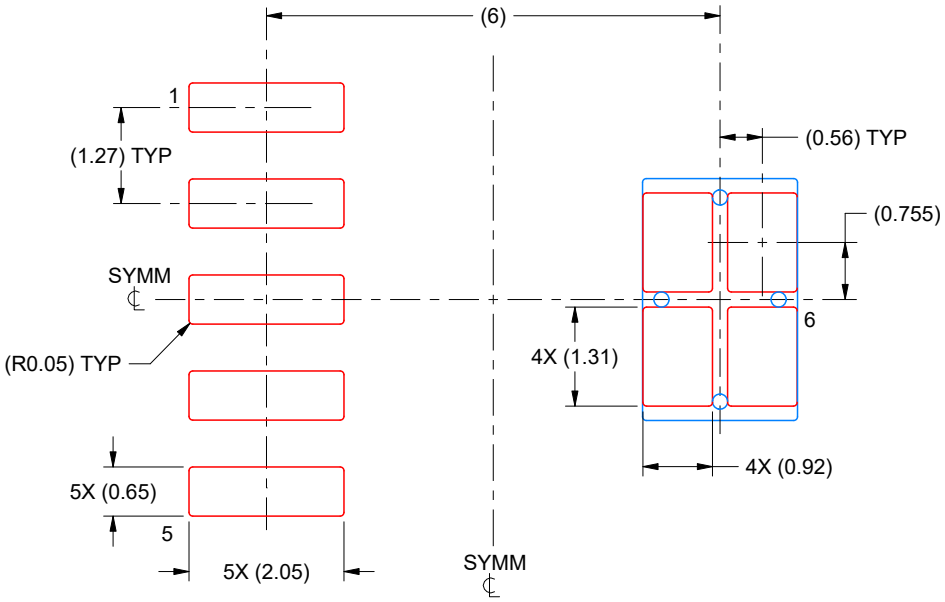


SOLDER MASK DETAILS

4214845/C 11/2021

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
6. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

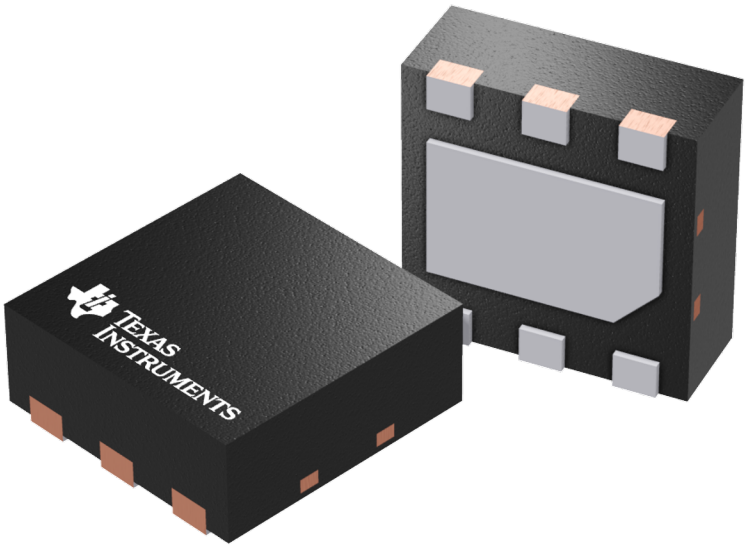
4214845/C 11/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

DRV 6 WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



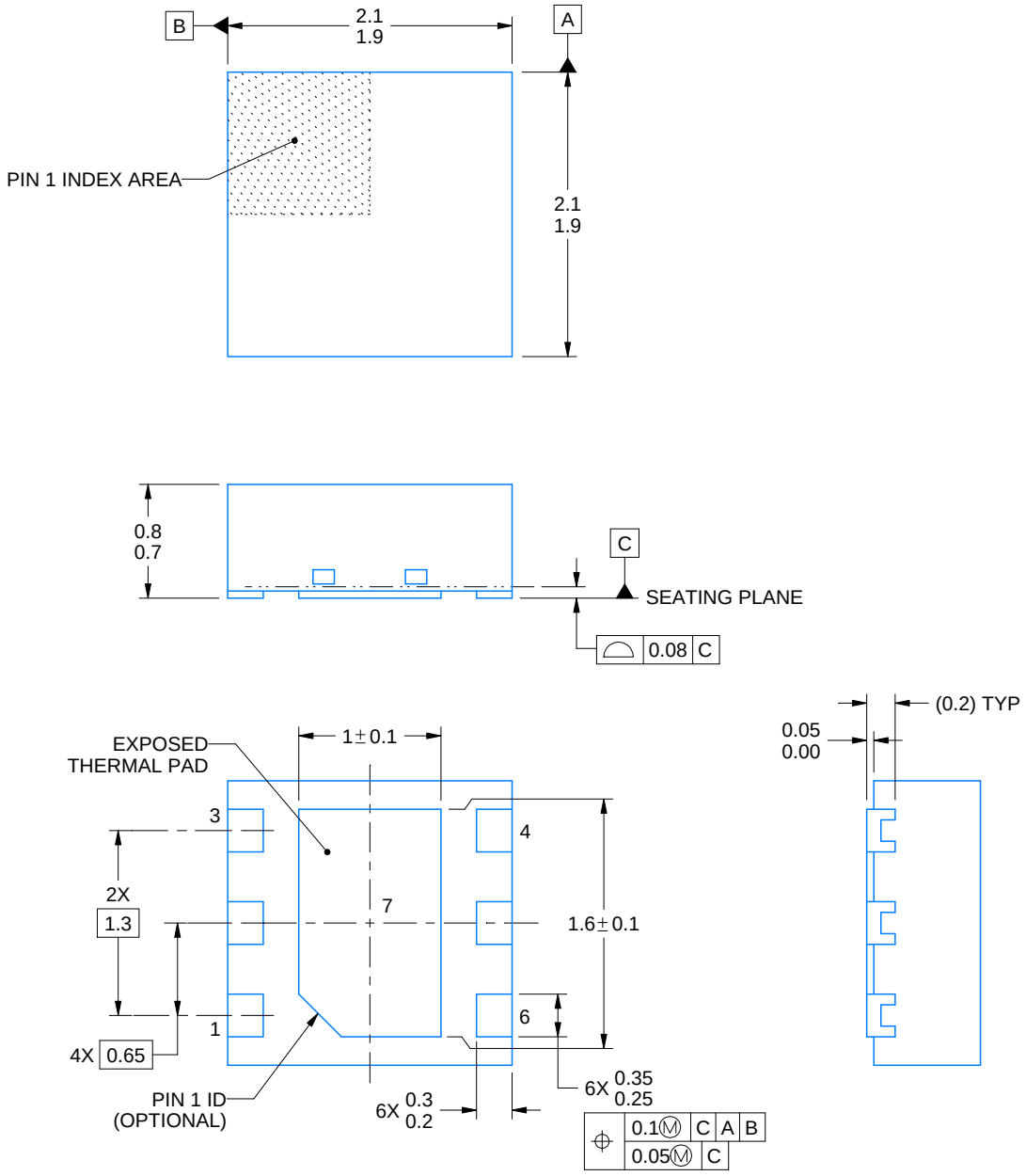
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

DRV0006D

PACKAGE OUTLINE

WSON - 0.8 mm max height

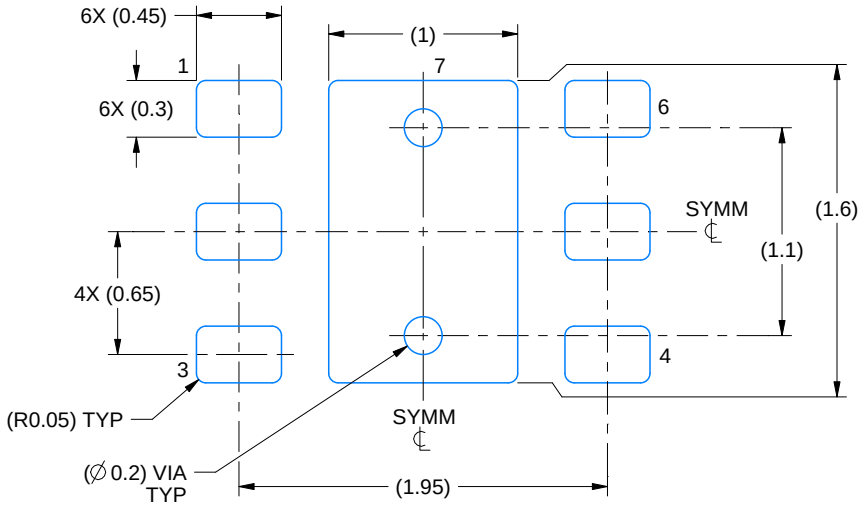
PLASTIC SMALL OUTLINE - NO LEAD



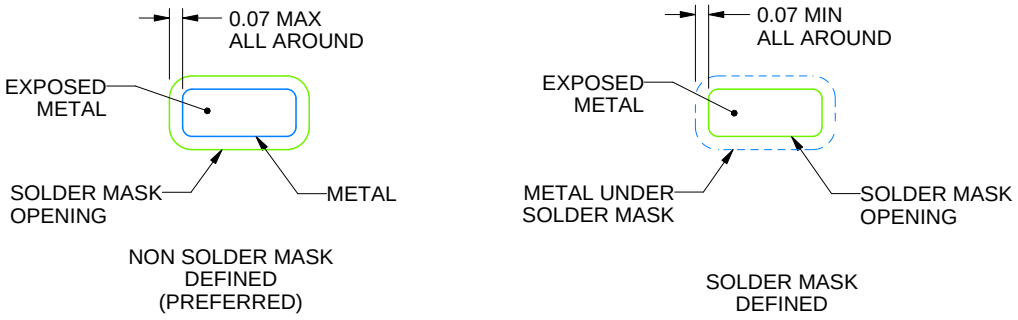
4225563/A 12/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:25X

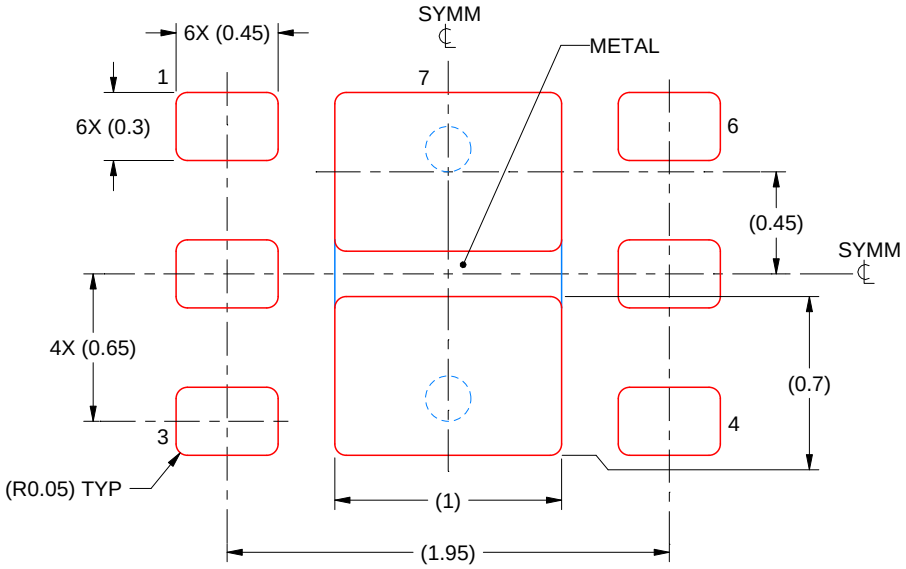


SOLDER MASK DETAILS

4225563/A 12/2019

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD #7
88% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:30X

4225563/A 12/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要声明和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2022，德州仪器 (TI) 公司